

ABSTRACT OF THE DISCLOSURE

The present invention is a method for producing a single crystal of which a whole plane in a radial direction is a defect-free region with pulling the single crystal from a raw material melt in a chamber by Czochralski method, wherein a pulling condition is changed in a direction of the crystal growth axis during pulling the single crystal so that a margin of a pulling rate is always a predetermined value or more that the single crystal of which the whole plane in a radial direction is a defect-free region can be pulled. Thereby, there can be provided a method for producing a single crystal in which when a single crystal is produced by CZ method, the single crystal of which a whole plane in a radial direction is a defect-free region entirely in a direction of the crystal growth axis can be produced with stability.